

TrenchT4™ **Power MOSFET**

IXTA380N036T4-7

= 36V380A $1.0 m\Omega$

N-Channel Enhancement Mode Avalanche Rated



	P D
(H
8 1/	
	J_{s}

TO-263 (7-lead)

Pins: 1 - Gate 2, 3, 5, 6, 7 - Source 4 (Tab) - Drain

Symbol	Test Conditions	Maximum Ratings		
V _{DSS}	$T_{_{\rm J}}$ = 25°C to 175°C	36	V	
V _{DGR}	$T_J = 25^{\circ}C$ to 175°C, $R_{GS} = 1M\Omega$	36	V	
V _{GSM}	Transient	±15	V	
I _{D25}	T _c = 25°C	380	Α	
LRMS	Lead Current Limit, RMS	160	Α	
I _{DM}	$T_{\rm C} = 25^{\circ}$ C, Pulse Width Limited by $T_{\rm JM}$	830	Α	
I _A	T _C = 25°C	190	Α	
E _{as}	$T_{c} = 25^{\circ}C$	1.4	J	
$\overline{\mathbf{P}_{D}}$	T _C = 25°C	480	W	
T		-55 +175	°C	
T_{JM}		175	°C	
T _{stg}		-55 +175	°C	
T,	Maximum Lead Temperature for Soldering	g 300	°C	
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C	
F _c	Mounting Force	10.65 / 2.214.6	N/lb	
Weight		3.0	g	

Features

- International Standard Package
- 175°C Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Low R_{DS(on)}

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converts & Off-Line UPS
- High Current Switching Applications
- Primary-Side Switch

SymbolTest ConditionsChar $(T_J = 25^{\circ}C \text{ Unless Otherwise Specified})$ Min.		acteristic Values Typ.			
BV _{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	36			V
V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
I _{GSS}	$V_{gs} = \pm 15V, V_{DS} = 0V$			±200	nA
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$			10	μΑ
	$T_{_{ m J}} = 150^{\circ}{ m C}$			750	μΑ
R _{DS(on)}	$V_{GS} = 10V, I_{D} = 100A, Note 1$			1.0	mΩ



•			acteristic Values		
$(1_{J} = 23)$	C, U	riless Otherwise Specified)	Min.	Тур.	Max.
\mathbf{g}_{fs}		$V_{DS} = 10V, I_{D} = 60A, \text{ Note } 1$	105	175	S
R _{Gi}		Gate Input Resistance		1.0	Ω
C _{iss})			13.4	nF
C _{oss}	}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		2400	pF
\mathbf{C}_{rss}	J			1650	pF
t _{d(on)})	Decisting Contabing Times		36	ns
t,		Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$		78	ns
t _{d(off)}		$R_{G} = 5\Omega$ (External)		125	ns
t _f	J	,		80	ns
Q _{g(on)})			260	nC
Q _{gs}	}	$V_{GS} = 10V$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_{D} = 0.5 \cdot I_{D25}$		60	nC
Q_{gd}	J			92	nC
R _{thJC}					0.31 °C/W

Source-Drain Diode

SymbolTest ConditionsChara $(T_J = 25^{\circ}C, Unless Otherwise Specified)$ Min.		cteristic Typ.	Values Max.		
I _s	$V_{GS} = 0V$			380	Α
I _{SM}	Repetitive, Pulse width limited by $\rm T_{_{\rm JM}}$			1520	Α
V_{SD}	$I_F = 100A, V_{GS} = 0V, \text{ Note 1}$			1.4	V
t _{rr}	$I_{\rm F} = 150 \text{A}, V_{\rm GS} = 0 \text{V}$		54		ns
I _{RM}	-di/dt = 100A/μs		2.6		Α
$Q_{_{\mathrm{RM}}}$	$V_R = 30V$		70		nC

Note 1: Pulse test, $t \le 300\mu s$, duty cycle, $d \le 2\%$.

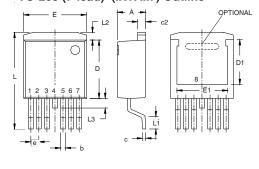
ADVANCE TECHNICAL INFORMATION

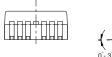
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

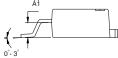


IXTA380N036T4-7

TO-263 (7-lead) (IXTA..7) Outline







Pins: 1 - Gate 2, 3, 5, 6, 7 - Source 4 - Drain

SYM	INCHES		MILLIMETER	
2114	MIN	MAX	MIN	MAX
А	.170	.185	4.30	4.70
Α1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
С	.016	.024	0.40	0.60
с2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386 .386	.402	9.80	10.20
E 1	.311	.319	7.90	8.10
е	.050 BSC		1.27BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2,30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

